EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	2	second adj nmos same logic adj core	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/10/17 13:56
L2	4	second adj nmos same Vcc same Vdd	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/10/17 13:58
L3	208	second adj nmos same level adj shift$3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/10/17 13:59
L4	4	second adj nmos same level adj shift$3 same operating near3 voltage	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/10/17 14:00
L5	1	second adj nmos same level adj shift$3 same operating near3 voltage	USPAT	OR	ON	2006/10/17 14:01
L6	30	second adj nmos same level adj shift$3 and operating near3 voltage	USPAT	OR	ON	2006/10/17 14:18
L7	12	second adj nmos same level adj shift$3 and operating near3 voltage and (logic near2 core internal near2 circuit)	USPAT	OR	ON	2006/10/17 14:17
L8	20	second adj nmos same level adj shift$3 and (core near2 logic internal near2 circuit)	USPAT	OR	ON	2006/10/17 14:19
L9	15	("20030102890" | "4808852" | "5204557" | "5559464" | "5669684" | "5995010" | "6034549" | "6064229" | "6208167" | "6232794" | "6242962" | "6268744" | "6522168" | "6650168" | "6836148"). PN.	US-PGPUB; USPAT; USOCR	OR	ON	2006/10/17 14:19

L11	50703	(First near2 voltage same second near2 voltage VCC same VDD) same output	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/10/17 16:15
L12	2654	(First near2 voltage same second near2 voltage VCC same VDD) same output near3 stage	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/10/17 16:15
L13	0	(First near2 voltage same second near2 voltage VCC same VDD) same output near3 stage same (core adj logic)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/10/17 16:16
L14	9	(First near2 voltage same second near2 voltage VCC same VDD) same output near3 stage same (core adj logic internal adj circuit)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/10/17 16:18
L15	9	(First near2 voltage same second near2 voltage Vdd1 same VDD) same output near3 stage same (core adj logic internal adj circuit)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/10/17 16:19
L16	6	(Vdd1 same VDD) same output near3 stage and (core adj logic internal adj circuit)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/10/17 16:20
L17	27	(Vdd1 same VDD) same output and (core adj logic internal adj circuit)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/10/17 16:23
L18	3	(Vdd1 same VDD) same output and (core adj logic internal adj circuit) and level near shift$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/10/17 16:25

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L19	166	nmos same cascode and level near shift$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/10/17 16:25
L20	111	nmos same cascode and level near shift$4	USPAT	OR	ON	2006/10/17 16:25
L21	64	nmos same cascode and level near shift$4 and operating with voltage	USPAT	OR	ON	2006/10/17 16:26
L22	36	nmos same cascode and level near shift$4 and operating near2 voltage	USPAT	OR	ON	2006/10/17 16:26
L23	7	nmos same cascode same level near shift$4 and operating near2 voltage	USPAT	OR	ON	2006/10/17 16:26
S1	2	"20050146819"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/18 16:26
S2	79	esd and input adj stage same output adj stage	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/16 12:07
S3	0	esd and input adj stage same output adj stage same doides	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/05/16 12:08
S4	2	esd and input adj stage same output adj stage same diodes	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/05/16 12:10
S5	43	esd and output adj stage same diodes	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/05/16 12:12

S6	0	esd and output adj stage same diodes same vow adj voltage	US-PGPUB ; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/05/16 12:13
S7	1	esd and output adj stage same diodes same low adj voltage	US-PGPUB ; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/05/16 12:13
S8	26	esd and output adj stage same diodes and low adj voltage	US-PGPUB ; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/05/16 12:13
S9	5	esd and output adj stage same diodes and low adj voltage and high adj voltage	US-PGPUB ; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/05/16 12:22
S10	2	esd and output adj stage same diodes same cmos and low adj voltage	US-PGPUB ; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/05/16 13:56
S11	2	esd and output adj stage same diodes same gate same cmos and low adj voltage	US-PGPUB ; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/05/16 14:09
S12	14	esd and output adj stage and low adj voltage and high adj voltage and intermediate adj voltage	US-PGPUB ; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/05/16 14:12
S13	91	esd and output adj stage and output with diode with gate	US-PGPUB ; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/05/16 14:13

S14	3	esd same output adj stage and output with diode with gate	US-PGPUB ; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/05/16 14:42
S15	19	protection same output adj stage and output and vcc and vdd	US-PGPUB ; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/05/16 14:44
S16	14	protection same output adj stage and output same diode and vcc and vdd	US-PGPUB ; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/16 14:46
S17	201	output adj stage and output same diode and vcc and vdd	US-PGPUB ; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/16 14:46
S18	176	output adj stage and output same diode and vcc and vdd and source and drain	US-PGPUB ; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/16 14:47
S19	137	output adj stage and output same diode same source and drain and vcc and vdd	US-PGPUB ; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/16 14:52
S20	1	output adj stage and output same diode same source and drain and vcc and vdd and vdd1	US-PGPUB ; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/16 14:48
S21	1	output adj stage and output same diode same source and drain and vcc and vdd2 and vdd1	US-PGPUB ; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/16 14:49

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S22	2	"5440244".pn.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/16 14:49
S23	1	"5440244".pn. and diode	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/16 14:50
S24	132	output adj stage and output same diode same source same drain same (cmos)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/16 14:52
S25	425	output adj stage and output same diode same source same drain same (cmos mos)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/16 15:24
S26	44	output adj stage and output same diode same source same drain same (cmos mos) same protect$3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/16 14:54
S27	20	output adj stage same output same diode same source same drain same (cmos mos) same protect$3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/16 14:54
S28	3	output adj stage same output same diode near2 gate same source same drain same (cmos mos) same protect$3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/16 15:04
S29	2	"5867010".pn.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/16 15:06

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S30	2	"5844425".pn.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/16 15:06
S31	129	output adj stage and output same diode same source same drain same (cmos mos) and transient	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/16 15:28
S32	3	output adj stage and output same diode same source same drain same (cmos mos) and transient and 361/56.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/16 15:29
S33	8	output adj stage and output same diode same source same drain same (cmos mos) and 361/56.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/16 16:09
S34	1	kirhoff	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/16 16:12
S35	3259	kirchhoff	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/16 16:12
S36	52760	output adj stage	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/18 16:27
S37	7586	S36 same diode	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/18 16:27

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S38	405	S37 same protection	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/18 16:28
S39	14	S38 same cmos	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/18 16:28
S40	1263	326/80,81.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/20 11:40
S41	0	326/80,81.ccls. same cmos same saturation	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/20 11:41
S42	6	326/80,81.ccls. and cmos same saturation	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/20 11:44
S43	93	326/80,81.ccls. and cmos same diode	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/20 11:45
S44	57	326/80,81.ccls. and cmos same diode same output	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/20 11:45
S45	15	326/80,81.ccls. and cmos same diode same output near4 (stage node)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/20 11:52

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S46	1	"7046036".pn.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/20 11:53
S47	2	("6201428" | "6388475").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2006/05/20 11:55
S48	3	("6201428").URPN.	USPAT	OR	ON	2006/05/20 11:56
S49	6	("6388475").URPN.	USPAT	OR	ON	2006/05/20 11:57
S50	2	("6201428" | "6388475").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2006/05/20 11:59
S51	1737	cmos same ttl same level	US-PGPUB; USPAT; USOCR	OR	ON	2006/05/20 12:00
S52	1131451	cmos same ttl same levelnear2 shift$3	US-PGPUB; USPAT; USOCR	OR	ON	2006/05/20 12:00
S53	178	cmos same ttl same level near2 shift$3	US-PGPUB; USPAT; USOCR	OR	ON	2006/05/20 12:01
S54	1	cmos same ttl same level near2 shift$3 same core	US-PGPUB; USPAT; USOCR	OR	ON	2006/05/20 12:01
S55	9	cmos same ttl same level near2 shift$3 and gate near3 diode	US-PGPUB; USPAT; USOCR	OR	ON	2006/05/20 12:04
S56	91	cmos same ttl same level near2 shift$3 and bias$4	US-PGPUB; USPAT; USOCR	OR	ON	2006/05/20 12:04
S57	14	cmos same ttl same level near2 shift$3 same bias$4	US-PGPUB; USPAT; USOCR	OR	ON	2006/05/20 12:07
S58	2	cmos same ttl same level near2 shift$3 same bias$4 same diode	US-PGPUB; USPAT; USOCR	OR	ON	2006/05/20 12:09
S59	32	cmos same level near2 shift$3 same bias$4 same diode	US-PGPUB; USPAT; USOCR	OR	ON	2006/05/20 12:10
S60	3	cmos same level near2 shift$3 same bias$4 same diode and protection	US-PGPUB; USPAT; USOCR	OR	ON	2006/05/20 12:11
S61	0	cmos same level near2 shift$3 same bias$4 same diode with gate and protection	US-PGPUB; USPAT; USOCR	OR	ON	2006/05/20 12:11

S62	7	cmos same level near2 shift$3 same bias$4 same diode with gate	US-PGPUB ; USPAT; USOCR	OR	ON	2006/05/20 12:27
S63	1	cmos same level near2 shift$3 same bias$4 same diode near2 gate	US-PGPUB ; USPAT; USOCR	OR	ON	2006/05/20 12:27
S64	27	relatively adj high adj voltage	US-PGPUB ; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/20 12:54
S65	1	relatively adj high adj voltage and relatively adj low adj voltage	US-PGPUB ; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/20 12:52
S66	1	relatively adj high near voltage and relatively adj low near voltage	US-PGPUB ; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/20 12:52
S67	0	relatively adj high near voltage and relatively adj low near voltage	US-PGPUB	OR	ON	2006/05/20 12:53
S68	0	relatively adj high near voltage and "20050146819"	US-PGPUB	OR	ON	2006/05/20 12:53
S69	0	relatively near high near voltage and "20050146819"	US-PGPUB	OR	ON	2006/05/20 12:53
S70	1	"20050146819"	US-PGPUB	OR	ON	2006/05/20 12:54
S71	0	"20050146819" and "relatively low voltage"	US-PGPUB	OR	ON	2006/05/20 12:54
S72	32	relatively adj low adj voltage	US-PGPUB ; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/20 13:00
S73	1	S72 and S64	US-PGPUB ; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/20 12:56

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S74	54	relatively near2 low near2 voltage	US-PGPUB ; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/20 13:00
S75	45	relatively near2 high near2 voltage	US-PGPUB ; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/20 13:01
S76	5	S74 and S75	US-PGPUB ; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/20 13:00
S77	0	(relatively near2 high near2 voltage).clm.	US-PGPUB ; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/20 13:01
S78	0	(relatively near2 low near2 voltage).clm.	US-PGPUB ; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/20 13:01
S79	0	(relatively with low with voltage).clm.	US-PGPUB ; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/20 13:01
S80	12	second adj nmos same saturated	US-PGPUB ; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/10/16 15:55
S81	0	second adj nmos same saturated same third adj nmos	US-PGPUB ; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/10/16 15:43

S82	176	second adj nmos and saturated	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/10/16 15:54
S83	58	second adj nmos same saturat$3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/10/16 15:55
S84	23	second adj nmos same saturat$3 and third adj nmos	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/10/16 15:57
S85	40	second adj nmos same saturat$3 and bias$3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/10/16 15:58
S86	11	second adj nmos same saturat$3 same bias$3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/10/17 13:55
S87	4	second adj nmos same saturat$3 same bias$3 and operation near3 voltage	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/10/17 10:06
S88	26	second adj (nmos mos fet mosfet) same saturat$3 same bias$3 and operation near3 voltage	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/10/17 10:09
S89	96	second with (nmos mos fet mosfet) same saturat$3 same bias$3 and operation near3 voltage	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/10/17 10:09

| S90 | 14 | second with (nmos mos fet mosfet) same saturat$3 same bias$3 same operation near3 voltage | US-PGPUB ; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/10/17 10:09 |
| S91 | 17 | second with (nmos mos fet mosfet) same saturat$3 same bias$3 same (operation operational) near3 voltage | US-PGPUB ; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/10/17 10:10 |